

## ABSTRACT OF THE DISCLOSURE

In a transistor adapted to suppress characteristic degradation resulting from fluorine contained in a deposited film, the concentration of fluorine contained in a gate insulating film (3) is reduced to  $1.0 \times 10^{20}$  atoms/cm<sup>3</sup> or less. As a result, the transistor can provide excellent  
5 reliability even when it is continuously driven for a long period of time at a relatively high temperature.